

D25XB100

PRV : 1000 Volts
Io : 25 Amperes

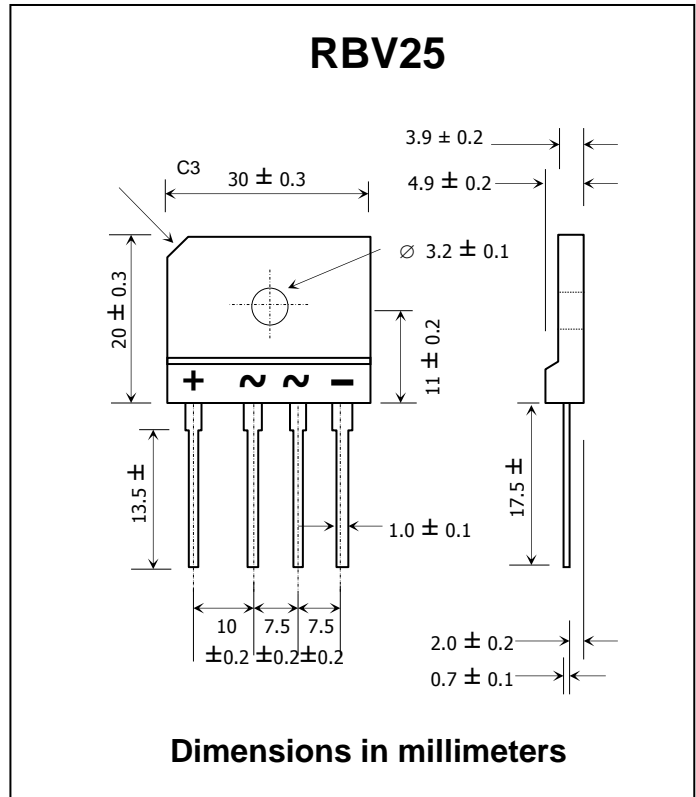
FEATURES :

- * High current capability
- * High surge current capability
- * High reliability
- * Low reverse current
- * Low forward voltage drop
- * Ideal for printed circuit board
- * Very good heat dissipation
- * Pb / RoHS Free

MECHANICAL DATA :

- * Case : Reliable low cost construction utilizing molded plastic technique
- * Epoxy : UL94V-O rate flame retardant
- * Terminals : Plated lead solderable per MIL-STD-202, Method 208 guaranteed
- * Polarity : Polarity symbols marked on case
- * Mounting position : Any

SILICON BRIDGE RECTIFIERS



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified.
 Single phase, half wave, 60 Hz, resistive or inductive load.
 For capacitive load, derate current by 20%.

RATING	SYMBOL	VALUE	UNIT
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	1000	V
Maximum RMS Voltage	V_{RMS}	700	V
Maximum DC Blocking Voltage	V_{DC}	1000	V
Maximum Average Forward Current 50 Hz sine wave, R-load	$I_{F(AV)}$	25 (With heatsink, $T_c = 87^\circ\text{C}$)	A
		3.5 (Without heatsink, $T_a = 25^\circ\text{C}$)	
Peak Forward Surge Current, 50Hz sine wave Non-repetitive 1 cycle peak value, $T_j = 25^\circ\text{C}$	I_{FSM}	300	A
Current Squared Time at $t < 8.3$ ms.	I^2t	373	A^2S
Maximum Forward Voltage per Diode at $I_F = 12.5$ A	V_F	1.1	V
Maximum DC Reverse Current $T_a = 25^\circ\text{C}$ at Rated DC Blocking Voltage	I_R	10	μA
Operating Junction Temperature Range	T_J	- 55 to + 150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	- 55 to + 150	$^\circ\text{C}$



RATING AND CHARACTERISTIC CURVES (D25XB100)

FIG.1 - DERATING CURVE FOR OUTPUT RECTIFIED CURRENT

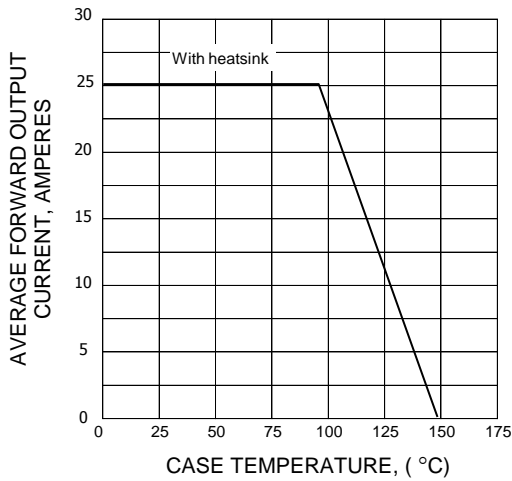


FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

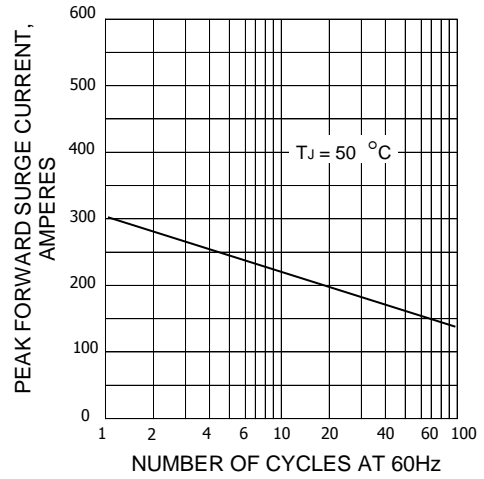


FIG.3 - TYPICAL FORWARD CHARACTERISTICS PER DIODE

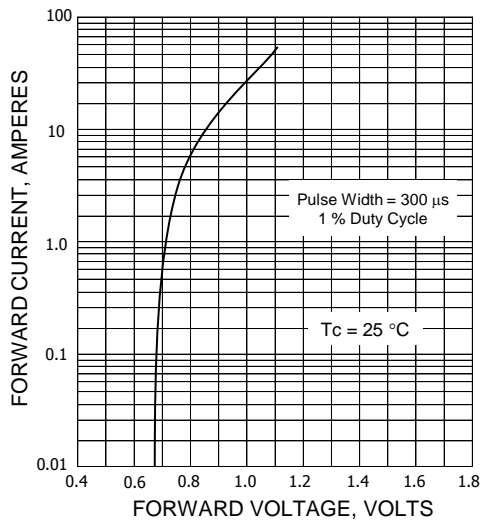


FIG.4 - TYPICAL REVERSE CHARACTERISTICS PER DIODE

